

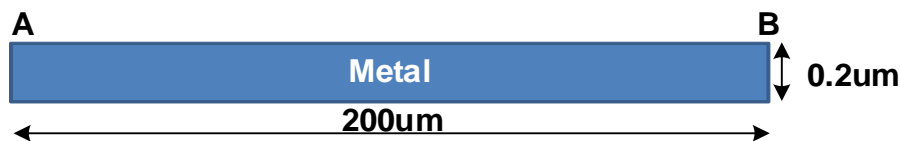
**National University of Singapore**  
**Electrical and Computer Engineering**  
**CG2027 (Transistor-Level Digital Circuits)**  
**Assignment #2 Solution**

AY21/22 Semester 1  
Issued: Aug. 17, 2021

Due: Aug. 22, 2021 (18:00)

**Problem 1: Load Estimate (Capacitance and Resistance)**

We assume a wire length of 200 $\mu\text{m}$ , and width of 0.2 $\mu\text{m}$ .



- a) Calculate the value of  $C_{\text{wire}}$  for the wire segment A to B of the metal. Assume area capacitance is 19 aF/ $\mu\text{m}^2$ , and fringe capacitance is 61 aF/ $\mu\text{m}$ .

→ Area Capacitance =  $(19 \text{ aF}/\mu\text{m}^2) * 200 \mu\text{m} * 0.2 \mu\text{m} = 0.76 \text{ fF}$

Fringe Capacitance =  $(61 \text{ aF}/\mu\text{m}) * 200 \mu\text{m} * 2 = 24.4 \text{ fF}$

$C_{\text{Total}} = C_{\text{Area}} + C_{\text{Fringe}} = 0.76 \text{ fF} + 24.4 \text{ fF} = \mathbf{25.16 \text{ fF}}$ .

- b) Calculate the value of  $R_{\text{wire}}$  for the segment A to B. Assume the sheet resistance of the metal is given as 0.04/ $\square$ .

→ Wire Resistance =  $(0.04 \text{ ohm}/\square) * 200 \mu\text{m} / 0.2 \mu\text{m} = \mathbf{40 \text{ ohm}}$

**Problem 2: Propagation Delay and IR Drop**

- a) For the wire given in Problem 1, assuming 4mA of current is flowing through the segment, what is the IR drop?

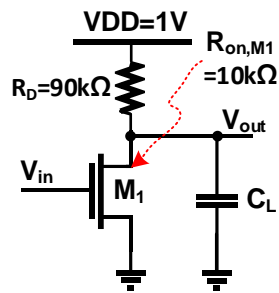
→ IR drop =  $4\text{mA} * 40 \text{ ohm} = \mathbf{160 \text{ (mV)}}$

- b) If a voltage source with 50 $\Omega$  output impedance is driving this wire segment, what is the propagation delay  $t_p$ ?

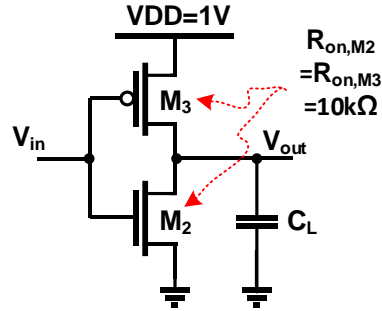
→  $t_p = 0.69RC = 0.69 * (50+40) \text{ ohm} * 25.16 * 10^{-15} = \mathbf{1.562 \text{ (ps)}}$  (5% difference allowed)

### Problem 3: Inverter Output Voltage

We assume two inverters: (a) an NMOS inverter with pull-up resistor, and (b) a CMOS inverter, as shown below. Assume the on resistance of all the transistors (M1-M3) is  $10\text{k}\Omega$ .



(a) NMOS inverter with pull-up resistor



(b) CMOS inverter

- a) For the NMOS inverter shown in the figure 3 (a), what is the steady-state  $V_{out}$  value when  $V_{in}=0\text{V}$  and  $1\text{V}$ , respectively?

→ When  $V_{in}=0\text{V}$ , M1 is turned off, and  $V_{out}$  is charged to  $V_{DD}=1\text{V}$  through  $R_D$ . Therefore,  $V_{out}=1\text{V}$ .

→ When  $V_{in}=1\text{V}$ , M1 is turned on, and a voltage divider is formed between  $R_D$  ( $90\text{k}\Omega$ ) and  $R_{on,M1}$  ( $10\text{k}\Omega$ ). Therefore,  $V_{out}=1 \cdot (10\text{k}) / (10\text{k} + 90\text{k}) = 0.1\text{V}$ .

- b) For the CMOS inverter shown in Fig. 3(b), what is the steady-state  $V_{out}$  value when  $V_{in}=0\text{V}$  and  $1\text{V}$ , respectively?

→  $V_{in}=0\text{V}$ , M2 is turned off, and  $V_{out}$  is charged to  $V_{DD}=1\text{V}$  through M3. Therefore,  $V_{out}=1\text{V}$ .

→  $V_{in}=1\text{V}$ , M3 is turned off, and  $V_{out}$  is discharged to GND through M2. Therefore,  $V_{out}=0\text{V}$ .

Note the output voltage of the CMOS inverter is independent of the on resistance of M2 and M3.